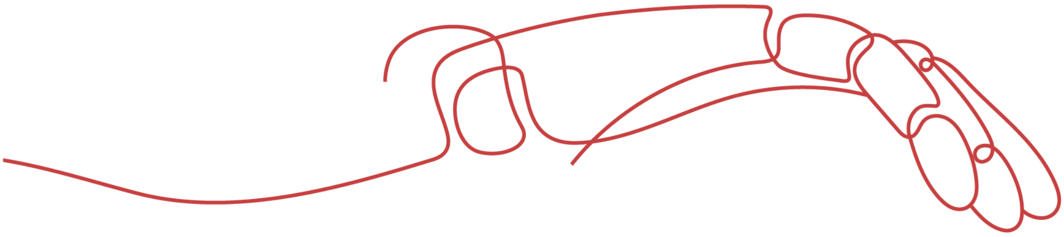
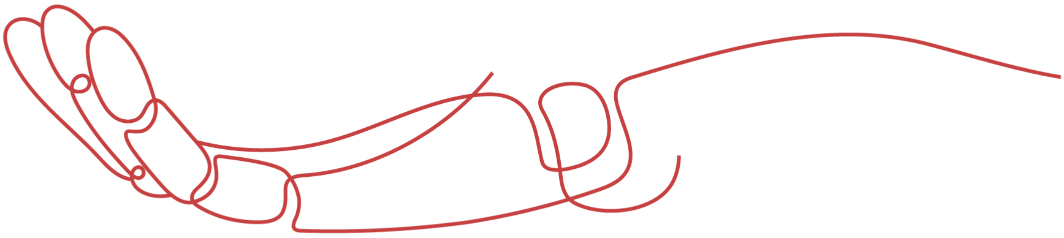
JG® Techology



PRODUCT DATA SHEET



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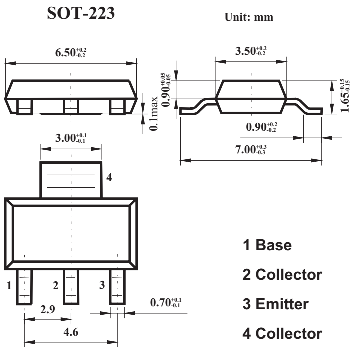
Datasheet **Resources** **Samples**

FZT657

NPN Silicon Planar Medium Power Transistor

■ Features

- ● Low saturation voltage



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	1	A
Continuous Collector Current	I_C	0.5	A
Power Dissipation at T_{amb}=25℃	P_{tot}	2	W
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ.	Max	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=100μA	300			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=10mA*	300			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=100μA	5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=200V			0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=3V			0.1	μA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=100mA, I_B=10mA*			0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=100mA, I_B=10mA*			1.0	V
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	I_C=100mA, V_{CE} =5V*			1.0	V
Static Forward Current Transfer Ratio	h_{FE}	I_C=10mA, V_{CE} =5V*	40			
		I_C=100mA, V_{CE} =5V*	50			
Transition Frequency	f_T	I_C=10mA, V_{CE} =20V,f=20MHz	30			MHz
Output Capacitance	C_{obo}	V_{CB} =20V, f=1MHz			20	pF

* Measured under pulsed conditions. Pulse Width=300μs. Duty cycle≤2%

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